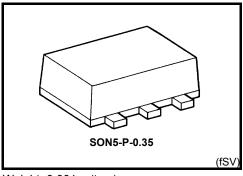
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7SG00AFS

2 Input NAND Gate

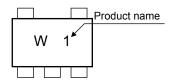
Features

- High-level output current: $I_{OH}/I_{OL} = \pm 8$ mA (min) at $V_{CC} = 3.0$ V
- High-speed operation: $t_{pd} = 2.5 \text{ ns (typ.)}$
 - at $V_{CC} = 3.3 \text{ V}, 15 \text{pF}$
- Operating voltage range: V_{CC} = 0.9~3.6 V
- 5.5-V tolerant inputs.

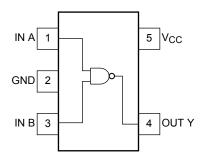


Weight: 0.001 g (typ.)

Marking



Pin Assignment (top view)



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Value	Unit
Power supply voltage	V _{CC}	V _{CC} −0.5~4.6	
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~ V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20 (Note 1)	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T _{stg}	-65~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Vout < GND, Vout > Vcc

Truth Table

Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

IEC Logic Symbol



Operating Ranges

Characteristics	Symbol	Value	Unit
Power supply voltage	V_{CC}	0.9~3.6	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Output Current		±8.0 (Note 2)	
		±4.0 (Note 3)	
	lou/lou	±3.0 (Note 4)	mA
	I _{OH} /I _{OL}	±1.7 (Note 5)	IIIA
		±0.3 (Note 6)	
		±0.02 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dV	0~10 (Note 8)	ns/V

Note 2: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 3: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 4: $V_{CC} = 1.65 \sim 1.95 \text{ V}$

Note 5: $V_{CC} = 1.4 \sim 1.6 \text{ V}$

Note 6: $V_{CC} = 1.1 \sim 1.3 \text{ V}$

Note 7: $V_{CC} = 0.9 \text{ V}$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

DC Electrical Characteristics

Characteristics Symbol		Toot Condition			٦	Γa = 25°0	2	Ta = -40~85°C		Unit
		Test Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
High-level VIH input voltage				0.9	V_{CC}	_	_	V _C C	_	
		_		1.1~1.3	V _{CC} × 0.7		_	V _{CC} × 0.7		V
	VIH			1.4~1.6	V _{CC} × 0.65	_	_	V _{CC} × 0.65	_	
			1.65~1.95	V _{CC} × 0.65	_	_	V _{CC} × 0.65	_		
				2.3~2.7	1.7		_	1.7	_	
				3.0~3.6	2.0		_	2.0	_	
				0.9			GND	_	GND	
				1.1~1.3		-	V _{CC} × 0.3	_	V _{CC} × 0.3	V
Low-level	V _{IL}		_			-	V _{CC} × 0.35	_	V _{CC} × 0.35	
input voltage			1.65~1.95	١	١	V _{CC} × 0.35		V _{CC} × 0.35		
			2.3~2.7			0.7		0.7		
				3.0~3.6		_	0.8		0.8	
		V _{IN} = V _{IH} or V _{IL}	I _{OH} =-0.02 mA	0.9	0.75	_	_	0.75	_	٧
High-level Vol			$I_{OH} = -0.3 \text{ mA}$	1.1~1.3	V _{CC} × 0.75	-	_	V _{CC} × 0.75	_	
	V _{OH}		$I_{OH} = -1.7 \text{ mA}$	1.4~1.6	V _{CC} × 0.75	_	_	V _{CC} × 0.75	_	
			$I_{OH} = -3.0 \text{ mA}$	1.65~ 1.95	V _{CC} -0.45	_	_	V _{CC} -0.45	_	
			$I_{OH} = -4.0 \text{ mA}$	2.3~2.7	2.0		_	2.0	_	
			I _{OH} = -8.0 mA	3.0~3.6	2.48	_	_	2.48	_	
Low-level Vo			$I_{OL} = 0.02 \text{ mA}$	0.9		_	0.1	_	0.1	V
			I _{OL} = 0.3 mA	1.1~1.3	_	_	V _{CC} × 0.25	_	V _{CC} × 0.25	
	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 1.7 mA	1.4~1.6	_	_	V _{CC} × 0.25	_	V _{CC} × 0.25	
			I _{OL} = 3.0 mA	1.65~ 1.95	_	_	0.45	_	0.45	
			I _{OL} = 4.0 mA	2.3~2.7	_	_	0.4	_	0.4	
			I _{OL} = 8.0 mA	3.0~3.6	_	_	0.4	_	0.4	
Input leakage current	I _{IN}	V _{IN} = 0~5.5V		0~3.6		_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	V _{IN} = V _{CC}	or GND	3.6	_	_	1.0	_	10.0	μА

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AC Electrical Characteristics (input $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40~85°C		Unit	
Onaracteristics			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
		C_L = 10 pF, R_L = 1 M Ω	0.9	_	26.9	_	_	_	
			1.1~1.3	_	10.9	18.4	1.0	34.2	
			1.4~1.6		5.9	8.5	1.0	10.0	
			1.65~ 1.95	١	4.5	6.2	1.0	6.7	
			2.3~2.7		2.9	3.9	1.0	4.4	
			3.0~3.6		2.2	3.1	1.0	3.7	
		$C_L = 15 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9		30.0	_	_		
	tpLH tpHL		1.1~1.3	_	12.0	21.5	1.0	37.2	ns
			1.4~1.6	_	6.5	9.3	1.0	11.2	
Propagation delay time			1.65~ 1.95		5.0	6.9	1.0	7.1	
			2.3~2.7		3.2	4.4	1.0	5.0	
			3.0~3.6		2.5	3.4	1.0	3.9	
		$C_L = 30 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	_	45.0	_		_	
			1.1~1.3	_	18.0	29.6	1.0	56.0	
			1.4~1.6	_	8.9	13.1	1.0	15.9	
			1.65~ 1.95		6.9	9.2	1.0	9.6	
			2.3~2.7	_	4.4	5.7	1.0	6.1	
			3.0~3.6	_	3.5	4.4	1.0	4.8	
Input capacitance	C _{IN}	_	3.6		3	_	_		pF
Power dissipation capacitance	C _{PD}	(Note9)	0.9~3.6	_	6	_		_	pF

Note 9: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

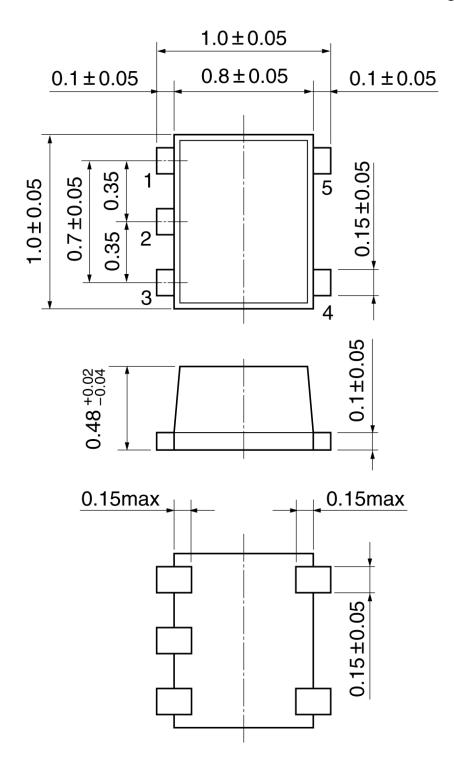
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Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Package Dimensions

SON5-P-0.35 Unit:mm



Weight: 0.001 g (typ.)

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20070701-EN GENERAL

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